

Features

- Operate from 1.65V to 5.5V
- Inputs accept voltages to 5.5V
- High Noise Immunity
- Low power dissipation
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)
- SOT23-5 Package Available
- SOT353 Package Available

General Description

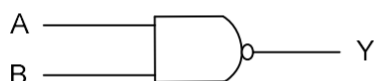
The 74LVC1G00 is a 2-input NAND gate device which provides the Function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

This device has power-down protective circuit preventing device from destruction when it is powered down.

Ordering Information

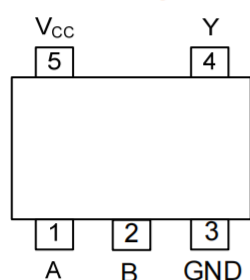
ORDER NUMBER	PACKAGE DESCRIPTION	PACKAGE OPTION
74LVC1G00GV	SOT23-5	Tape and Reel,3000
74LVC1G00GW	SOT353	Tape and Reel,3000

Logic Diagram



Logic symbol

Pin Configuration



SOT-23-5
SOT-353

Marking

74LVC1G00GV Marking:V00

74LVC1G00GW Marking:VA

Function Table

INPUT(A)	INPUT(B)	OUTPUT(Y)
H	H	L
H	L	H
L	H	H
L	L	H

Note: H: HIGH voltage level; L: LOW voltage level.

Absolute Maximum Ratings

PARAMETER	SYMBOL	CONDITIONS	RATINGS	UNIT
Supply Voltage	V_{CC}		-0.5 ~ +6.5	V
Input Voltage	V_{IN}		-0.5 ~ +6.5	V
Output Voltage	V_{OUT}	Output in the Power-off state	-0.5 ~ +6.5	V
		Output in the High or Low state	-0.5 ~ $V_{CC}+0.5$	V
V_{CC} or GND Current	I_{CC}	Output in the Power-off state	±100	mA
Continuous Output Current	I_{OUT}	$V_{OUT}=0\sim V_{CC}$	±50	mA
Input Clamp Current	I_{IK}	$V_{IN}<0$	-50	mA
Output Clamp Current	I_{OK}	$V_{OUT}<0$	-50	mA
Storage Temperature Range	T_{STG}		-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Thermal Data

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-23-5	θ_{JC}	280	°C/W
	SOT-353		350	

Recommended Operating Conditions

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Voltage	V_{CC}	Operating	1.65		5.5	V
		Data retention only	1.5			V
Input Voltage	V_{IN}		0		5.5	V
Output Voltage	V_{OUT}	High or Low state	0		V_{CC}	V
High-level Output Current	I_{OH}	$V_{CC}=1.65V$			-4	mA
		$V_{CC}=2.3V$			-8	mA
		$V_{CC}=3V$			-16	mA
		$V_{CC}=3V$			-24	mA
		$V_{CC}=4.5V$			-32	mA
Low-level Output Current	I_{OL}	$V_{CC}=1.65V$			4	mA
		$V_{CC}=2.3V$			8	mA
		$V_{CC}=3V$			16	mA
		$V_{CC}=3V$			24	mA
		$V_{CC}=4.5V$			32	mA
Input Transition Rise or Fall Rate	t_R / t_F	$V_{CC}=1.8V\pm0.15V, 2.5V\pm0.2V$			20	ns/V
		$V_{CC}=3.3V\pm0.3V$			10	ns/V
		$V_{CC}=5V\pm0.5V$			5	ns/V
Operating Temperature	T_A		-40		+125	°C

Electrical Characteristics

PARAMETER	SYMBOL	TEST CONDITIONS	T _A =25°C			T _A =-40~+125°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
High-Level Input Voltage	V _{IH}	V _{CC} =1.65V~1.95V	0.65 ×V _{CC}			0.65 ×V _{CC}			V
		V _{CC} =2.3V~2.7V	1.7			1.7			V
		V _{CC} =3V~3.6V	2			2			V
		V _{CC} =4.5V~5.5V	0.7 ×V _{CC}			0.7 ×V _{CC}			V
Low-Level Input Voltage	V _{IL}	V _{CC} =1.65V~1.95V			0.35 ×V _{CC}			0.35 ×V _{CC}	V
		V _{CC} =2.3V~2.7V			0.7			0.7	V
		V _{CC} =3V~3.6V			0.8			0.8	V
		V _{CC} =4.5V~5.5V			0.3 ×V _{CC}			0.3 ×V _{CC}	V
High-Level Output Voltage	V _{OH}	V _{CC} =1.65~5.5V, I _{OH} =-100μA	V _{CC} -0.1			V _{CC} -0.1			V
		V _{CC} =1.65V, I _{OH} =-4mA	1.2			0.95			V
		V _{CC} =2.3V, I _{OH} =-8mA	1.9			1.7			V
		V _{CC} =3.0V, I _{OH} =-16mA	2.4			1.9			V
		V _{CC} =3.0V, I _{OH} =-24mA	2.3			2.0			V
		V _{CC} =4.5V, I _{OH} =-32mA	3.8			3.4			V
Low-Level Output Voltage	V _{OL}	V _{CC} =1.65~5.5V, I _{OL} =100μA			0.1			0.1	V
		V _{CC} =1.65V, I _{OL} =4mA			0.45			0.7	V
		V _{CC} =2.3V, I _{OL} =8mA			0.3			0.45	V
		V _{CC} =3.0V, I _{OL} =16mA			0.4			0.6	V
		V _{CC} =3.0V, I _{OL} =24mA			0.55			0.80	V
		V _{CC} =4.5V, I _{OL} =32mA			0.55			0.80	V
Input Leakage Current	I _{I(LEAK)}	V _{IN} =5.5V or GND, V _{CC} =0 ~ 5.5V			±5			±5	μA
Power OFF Leakage Current	I _{OFF}	V _{IN} or V _{OUT} =5.5V, V _{CC} =0V			±10			±10	μA
Quiescent Supply Current	I _Q	V _{IN} =V _{CC} or GND, I _{OUT} =0, V _{CC} =1.65~5.5V			10			10	μA
Additional Quiescent Supply Current Per Input Pin	ΔI _Q	V _{CC} =3~5.5V, One input at V _{CC} -0.6V, Other inputs at V _{CC} or GND			500			500	μA

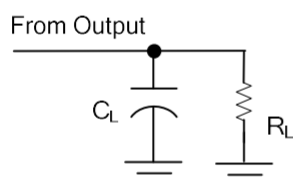
Dynamic Characteristics (Input: t_R, t_F≤3ns; P_{RR}≤1MHz)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A =25°C			T _A =-40~+125°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
Propagation delay from input (A or B) to output(Y)	t _{PLH} / t _{PHL}	V _{CC} =1.8±0.15V	C _L =15pF R _L =1MΩ	1.0	8.2	1.0		9.7	ns
		V _{CC} =2.5±0.2V		0.5	5.4	0.5		6.9	ns
		V _{CC} =3.3±0.3V		0.5	4.8	0.5		6.3	ns
		V _{CC} =5±0.5V		0.5	4.4	0.5		5.9	ns
		V _{CC} =1.8±0.15V, R _L =1KΩ	C _L =30pF	1.0	11	1.0		12	ns
		V _{CC} =2.5±0.2V, R _L =500Ω		0.5	7	0.5		9	ns
		V _{CC} =3.3±0.3V, R _L =500Ω		0.5	6.2	0.5		8.2	ns
		V _{CC} =5±0.5V, R _L =500Ω		0.5	5.1	0.5		6.5	ns

Operating Characteristics

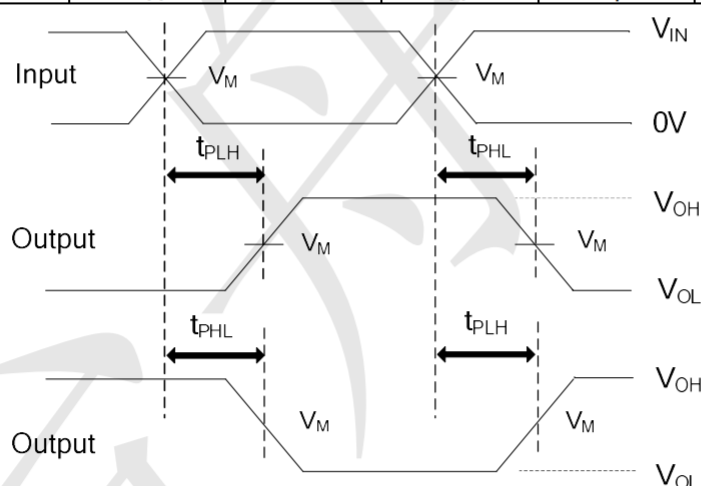
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Capacitance	C_i	$V_{CC}=3.3V$, $V_{IN}=V_{CC}$ or GND		4		pF
Power Dissipation Capacitance	C_{PD}	$V_{CC}=1.8V$		22		pF
		$V_{CC}=2.5V$		22		pF
		$V_{CC}=3.3V$		23		pF
		$V_{CC}=5.0V$		25		pF

Test Circuit And Waveforms



TEST CIRCUIT

V_{CC}	Inputs		V_M	C_L	R_L
	V_{IN}	t_R, t_F			
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	15pF	1M Ω
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	15pF	1M Ω
$3.3V \pm 0.3V$	3V	$\leq 2.5ns$	1.5V	15pF	1M Ω
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	15pF	1M Ω



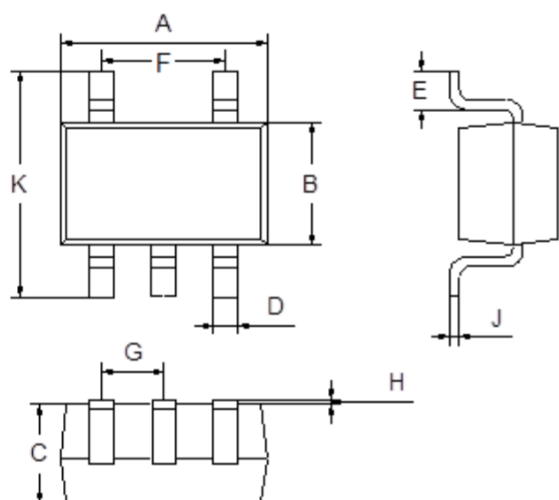
PROPAGATION DELAY TIMES

Note: C_L includes probe and jig capacitance.

All input pulses are supplied by generators having the following characteristics: $P_{RR} \leq 10MHz$, $Z_O = 50\Omega$.

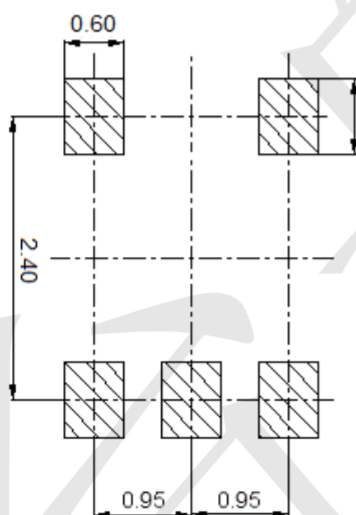
Package Outline Dimensions (Unit: mm)

SOT23-5



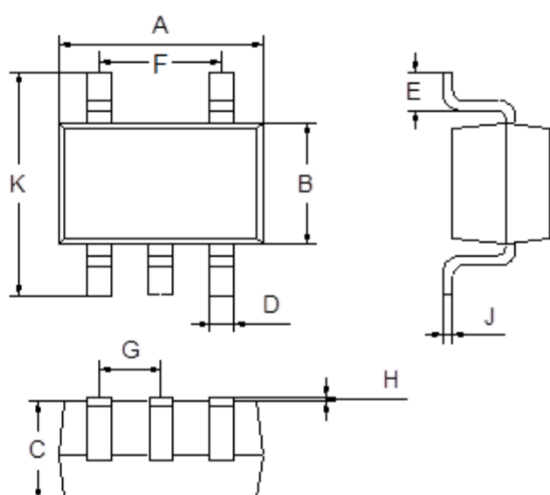
Dimension	Min.	Max.
A	2.80	3.00
B	1.50	1.70
C	1.00	1.20
D	0.35	0.45
E	0.35	0.55
F	1.80	2.00
G	0.90	1.00
H	0.02	0.10
J	0.10	0.20
K	2.60	3.00

Mounting Pad Layout (Unit: mm)



Package Outline Dimensions (Unit: mm)

SOT353



Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
F	1.20	1.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

